

In the Claims:

1 to 7 (Cancelled).

8. (Currently Amended) A method of polishing a patterned semiconductor substrate including the step of polishing the semiconductor substrate with a porous polishing pad, the porous polishing pad having a porous matrix formed from a coagulated polyurethane and a non-fibrous polishing layer, the non-fibrous polishing layer having a polishing surface with a pore count of at least 500 pores per mm^2 and the pore count (per mm^2) decreases below the polishing layer and a surface roughness Ra between 0.01 and 3 μm and maintaining the polishing surface with the pore count of at least 500 pores per mm^2 for at least 50 patterned wafers.

9. (Cancelled).

10. (Original) The method of claim 8 including the additional step of conditioning the porous polishing pad with a polymeric brush or polymeric pad.

11. (New) The method of claim 8 wherein the polishing occurs with a surface roughness Ra between 0.1 and 2 μm .

12. (New) The method of claim 8 including the additional step of applying a cutting tool to the upper surface.

13. (New) The method of claim 12 wherein the applying a cutting tool includes pressing a diamond conditioning head against the upper surface.

14. (New) A method of polishing a patterned semiconductor substrate including the step of polishing the semiconductor substrate with a porous polishing pad, the porous polishing pad having a porous matrix formed from a coagulated polyurethane and a non-fibrous polishing layer, the non-fibrous polishing layer having a polishing surface with a pore count of at least 500 pores per mm^2 and the pore count (per mm^2) decreases below the polishing layer and a

surface roughness Ra between 0.01 and 3 μm and maintaining the polishing surface with the pore count of 500 to 10,000 pores per mm^2 for at least 50 patterned wafers.

15. (New) The method of claim 14 wherein the porous polishing pad maintains a pore count of 500 to 2,500 pores per mm^2 for at least 50 patterned wafers.

16. (New) The method of claim 14 including the additional step of conditioning the porous polishing pad with a polymeric brush or polymeric pad.

17. (New) The method of claim 14 wherein the polishing occurs with a surface roughness Ra between 0.1 and 2 μm .

18. (New) The method of claim 14 including the additional step of applying a cutting tool to the upper surface.

19. (New) The method of claim 18 wherein the applying a cutting tool includes pressing a diamond conditioning head against the upper surface.